



The ZM160N10P combines advanced trench MOSFET technology with a low resistance package to provide extremely low R<sub>DS(ON)</sub> . This device is ideal for load switch

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T<sub>C</sub> =25

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	V
Continuous Drain Current	I <sub>D@TC=25</sub>	50	A
	I <sub>D@TC=75</sub>	38	A
	I <sub>D@TC=100</sub>	31.5	A
Pulsed Drain Current	I <sub>DM</sub>	150	A
Total Power Dissipation(TC=25 )	P <sub>D@TC=25</sub>	120	W
Operating Junction Temperature	T <sub>J</sub>	-55-150	
Storage Temperature Range	T <sub>STG</sub>	-55-150	





Fig.7 Switching Time Measurement Circuit

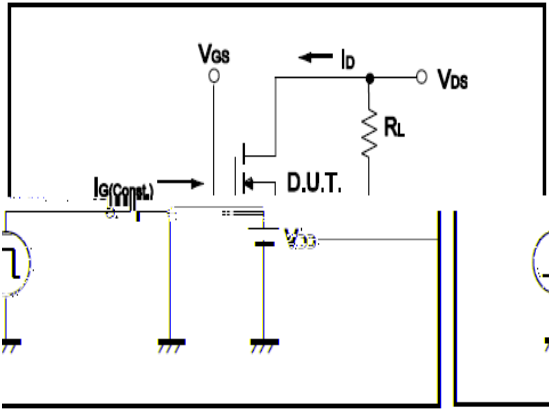


Fig.8 Gate Charge Waveform

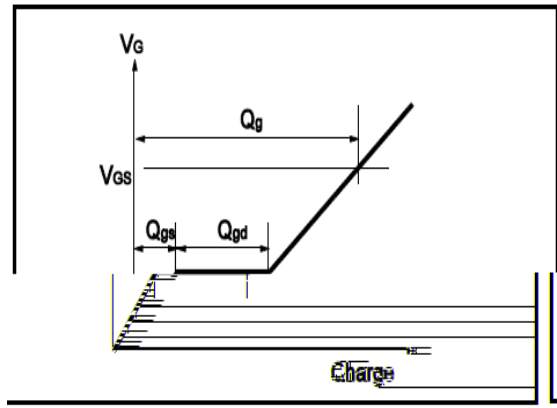


Fig.9 Switching Time Measurement Circuit

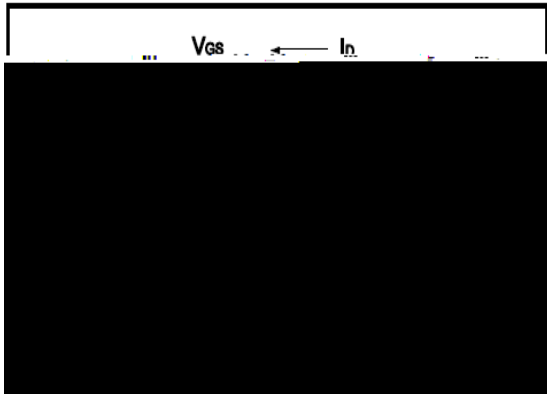


Fig.10 Gate Charge Waveform

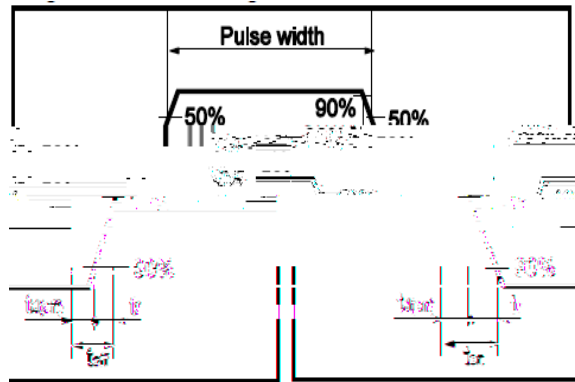


Fig.11 Avalanche Measurement Circuit

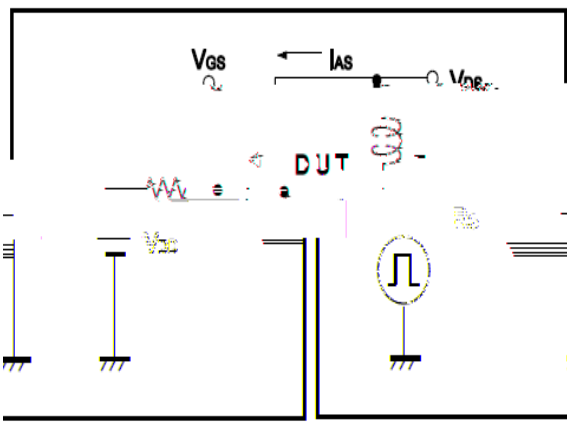
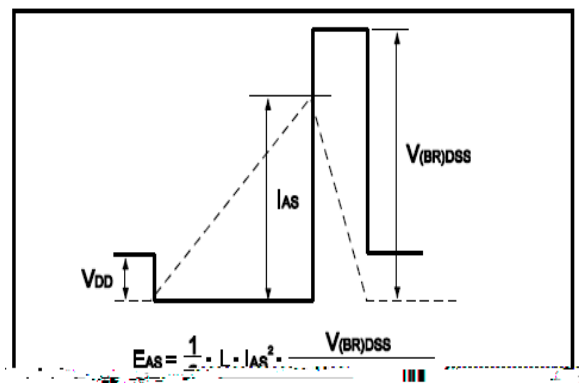


Fig.12 Avalanche Waveform





(TO-220)

Unit mm

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	.		.		0..		1..
					1 .		1 .

